

This diagram shows a cross-sectional view of a semiconductor device. A substrate 310 is at the base. A gate stack 320 is formed on the substrate. A first gate 330 is formed on the gate stack 320. A second gate stack 332 is formed on the first gate 330. A second gate 334 is formed on the second gate stack 332. A third gate 338 is formed on the second gate 334. A fourth gate 340 is formed on the third gate 338. A fifth gate 340 is formed on the fourth gate 338. A sixth gate 360 is formed on the fifth gate 340. A dashed line 334 indicates the boundary between the first gate 330 and the second gate stack 332.